TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# SSM6N04FU

## **High Speed Switch Applications**

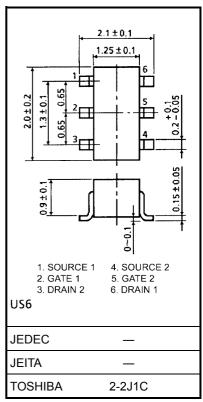
Unit: mm

- With built-in gate-source resistor:  $R_{GS} = 1 M\Omega$  (typ.)
- 2.5 V gate drive
- Low gate threshold voltage:  $V_{th} = 0.7 \sim 1.3 \text{ V}$
- Small package

## Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

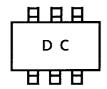
Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DS}$	20	V
Gate-source voltage	$V_{GSS}$	10	V
DC drain current	I <sub>D</sub>	100	mA
Drain power dissipation	P <sub>D</sub> (Note)	200	mW
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

Note: Total rating

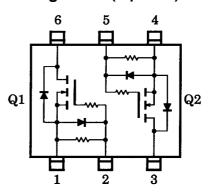


Weight: 6.8 mg (typ.)

## Marking

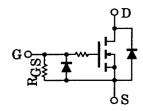


## Pin Assignment (top view)



(Q1, Q2 common)

## **Equivalent Circuit**



## Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage curre	ent	I <sub>GSS</sub>	$V_{GS} = 10 \ V, \ V_{DS} = 0$	_	_	15	μА
Drain-source break	down voltage	V (BR) DSS	$I_D = 100 \ \mu A, \ V_{GS} = 0$	20	_	_	V
Drain cut-off currer	nt	I <sub>DSS</sub>	$V_{DS} = 20 \ V, \ V_{GS} = 0$	_	_	1	μΑ
Gate threshold volt	age	V <sub>th</sub>	V <sub>DS</sub> = 3 V, I <sub>D</sub> = 0.1 mA	0.7	_	1.3	V
Forward transfer ad	dmittance	Y <sub>fs</sub>	V <sub>DS</sub> = 3 V, I <sub>D</sub> = 10 mA	25	50	_	mS
Drain-source ON re	esistance	R <sub>DS</sub> (ON)	$I_D$ = 10 mA, $V_{GS}$ = 2.5 V	_	4	12	Ω
Input capacitance		C <sub>iss</sub>	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	11.0	_	pF
Reverse transfer ca	apacitance	C <sub>rss</sub>	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	3.3	_	pF
Output capacitance		Coss	$V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	9.3	_	pF
Switching time	Turn-on time	t <sub>on</sub>	$V_{DD} = 3 \text{ V}, I_D = 10 \text{ mA}, V_{GS} = 0~2.5 \text{ V}$	_	0.16	_	
	Turn-off time	t <sub>off</sub>	$V_{DD} = 3 \text{ V}, I_D = 10 \text{ mA}, V_{GS} = 0 \sim 2.5 \text{ V}$	_	0.19	_	μS
Gate-source resiste	or	R <sub>GS</sub>	V <sub>GS</sub> = 0~10 V	0.7	1.0	1.3	ΜΩ

## **Switching Time Test Circuit**

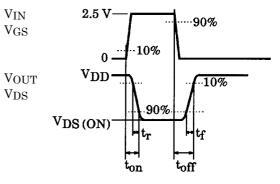
Test circuit

2.5 V

 $\begin{array}{c} OUT & VDD = 3 V \\ \hline \longrightarrow & D.U. \leq 1\% \end{array}$  $V_{IN}$ :  $t_r$ ,  $t_f < 5 \text{ ns}$ ( $Z_{out} = 50 \Omega$ ) COMMON SOURCE  $Ta = 25^{\circ}C$ 

(b)  $V_{IN}$  $V_{GS} \\$ 

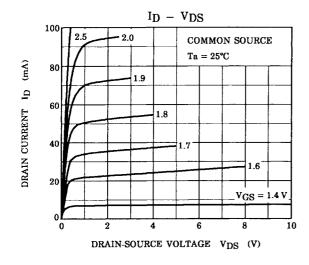
 $V_{\rm DS}$ 

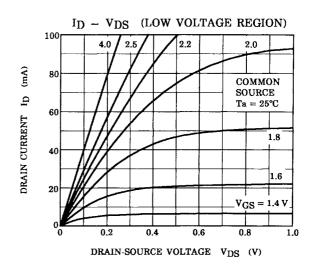


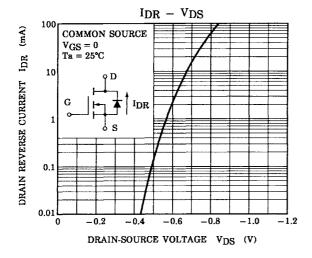
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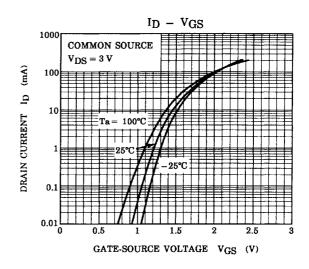
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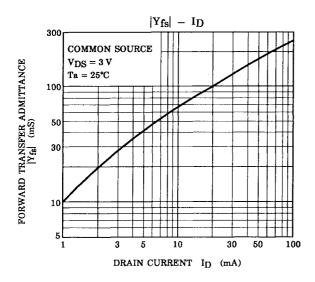
## (Q1, Q2 common)

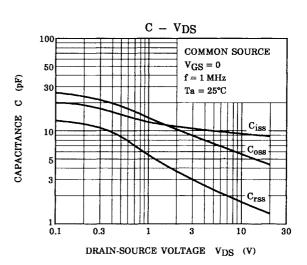






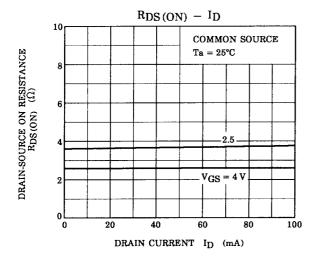


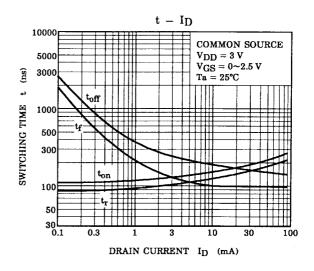


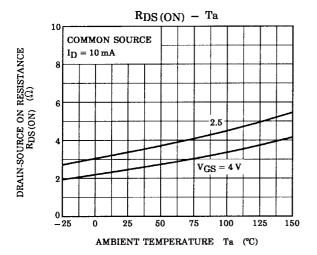


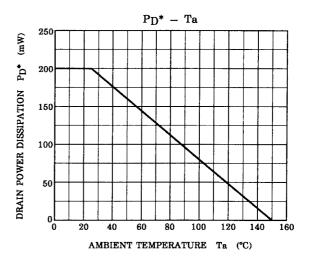
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## (Q1, Q2 common)









\*: Total rating

4

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5

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